

# SystemC-AMS Heterogeneous Modeling of a Capacitive Harvester of Vibration Energy

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## ABSTRACT

This paper presents the results of modeling of a mixed non-linear, strongly coupled and multidomain electromechanical system designed to scavenge the energy of ambient vibrations and to generate an electrical supply for an embedded microsystem. The system is operating in three domains: purely mechanical (the resonator), coupled electromechanical (electrostatic transducer associated with the moving mass) and electrical circuit, including switches, diodes and linear electrical components. Although only linear networks can be properly modeled in SystemC-AMS, we propose a technique allowing modeling of electrical networks including non-linear components (diodes) as well as time-varying capacitors. The whole system was modeled using two solvers of SystemC-AMS simultaneously: the one allowing TDF (Timed Data Flow) modeling and the one allowing LIN ELEC (linear electrical) circuit analysis. The modeling results are compared with VHDL-AMS and Matlab Simulink models.

## Keywords

Energy harvesting, SystemC-AMS, heterogeneous modeling, MEMS

## 1. INTRODUCTION

Capacitive harvesters require complex conditioning circuits which have a great impact on their energetic performances, and their optimization and modeling has been the subject of numerous studies [4][1]. A typical capacitive harvester includes:

- a mechanical resonator allowing an accumulation of the mechanical energy,
- an electrostatic (capacitive) transducer, with one electrode attached to a mobile mass, and the other fixed to the system which is submitted to external vibrations,

- a conditioning electrical circuit managing the flow of electrical charges on the transducer electrodes.

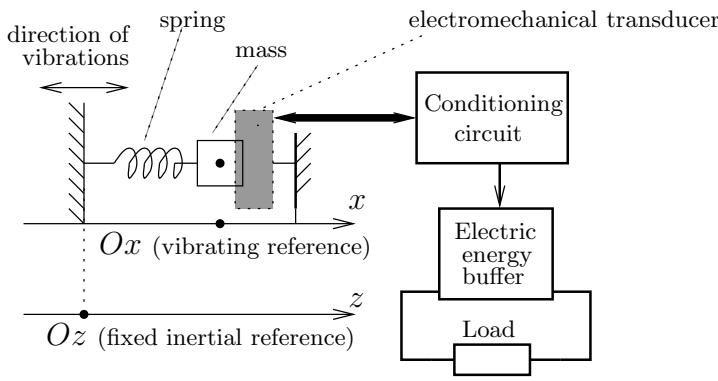
The paper presented at BMAS2007 conference reported on heterogeneous and mixed-domain modeling of such a system in a VHDL-AMS and Eldo environment (AdvanceMS platform) [3]. The theoretical study of the harvester system highlighted the need for a complex smart control electronics ensuring an optimal energy yield of the system [2]. This can be achieved by software blocks implemented in an embedded microcontroller. Strong links existing between electrical, mechanical and software blocks, as well as the real time operation of the system, require the use of reliable modeling tool allowing to model very heterogeneous systems together with software blocks.

The only platform satisfying these requirements is SystemC-AMS, which is an extension of SystemC for modeling analog and mixed systems. At the BMAS2007 conference was presented an advanced example of use of this platform for modeling a RF sensor network node, which included a sensor block, a microprocessor bloc and RF blocks [6].

The goal of this study is to build a SystemC-AMS model of mechanical harvester, which can be interfaced with a SystemC model describing complex digital electronics software blocks.

The development of a SystemC-AMS model of the harvester presented the following challenges:

- The existing beta-version of the SystemC-AMS library only provides the tools to build TDF models (Timed Data Flow, i.e., models composed of unidirectional Simulink-like blocks which can be non-linear) and linear electrical system models, including only linear electrical components. The use of non-linear electric element (e.g., diodes) is not allowed in the charge-conservative models of electrical circuits.
- Fixed step simulation engine: our system exhibits complex behaviour with different characteristic time constants, and the simulation time step has to be adapted to the quickest process.
- Modeling of highly non-linear elements (diodes) and discontinuous (switching) behaviour: the present version of SystemC-AMS does not include an algebraic solver allowing



**Figure 1: General structure of the vibration energy harvester.**

to resolve non-linear algebraic loops. Thus, to model such critical non-linear processes, the time step must be reduced, which leads to high modeling times.

In this work we highlight that these limitations can be circumvented using the SystemC-AMS mechanism allowing the connection between the linear conservative system domain and the TDF domain. This connection is possible thanks to the mechanism allowing the inclusion of components with time-varying parameters (resistor, capacitor, voltage and current source) in the linear circuit models. This connection does exist in both directions: a TDF domain signal can control the value of the resistance in a linear circuit, and an electrical value (current or voltage) measured in the linear circuit can be applied at the input of a TDF domain block also. In this paper we present how these features allow building a SystemC-AMS model of the harvester.

The paper is organized in the following way. In section 2 we briefly present the modeled system, in section 3 we present the models of all the blocks of the harvester and in section 4 we discuss the modeling results and compare them with a VHDL-AMS and a Simulink model.

## 2. SUMMARY OF ELECTROSTATIC HARVESTER OPERATION

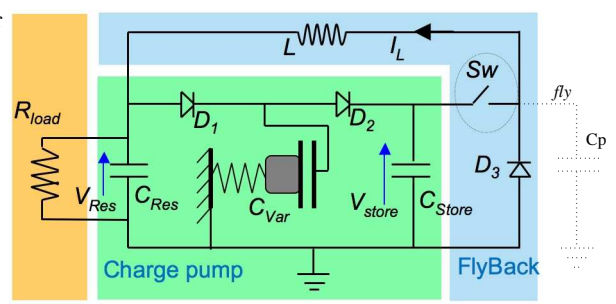
The modeled harvester can be seen as a conjunction of three blocks: the electromechanical resonant transducer including a resonator and a variable capacitor, a charge pump and a flyback circuit. The last two blocks are the parts of the conditioning circuit (Fig. 1).

### 2.1 Resonant electromechanical transducer

The idea of a vibration energy harvester using an electrostatic transducer is the following; the energy stored in the capacitor is given by:

$$W = \frac{Q^2}{2C}, \quad (1)$$

where  $Q$  is the charge,  $C$  is the capacitance. If  $C$  varies thanks to some mechanical force, it is possible to charge the capacitor when  $C$  is high (at the price of some energy  $W_1$ ), and discharge it when  $C$  is low (getting back some energy  $W_2$ ). From the formula (1) one obtains that  $W_2 > W_1$ , and



**Figure 2: Modeled conditioning circuit.**

that the difference  $W_2 - W_1$  corresponds to the energy harvested from the mechanical domain.

Fig. 3 presents the diagram of the resonant transducer block. The mechanical resonator accumulates the energy of external vibrations, the transducer ensures the transmission of the energy toward the electrical domain, i.e., the conditioning circuit. The mechanical part is modeled by a second-order lumped parameter system with stiffness  $k$ , damping  $\mu$  and mass  $m$ , and the capacitive transducer is a parallel-plate capacitor whose mobile electrode can move "in plane" [3]. In difference with the model presented in [3], in this work we used a capacitor whose capacitance varies linearly with the displacement (the numerical values are valid for the device presented in [5]), differently from the model presented in [3]:

$$C = 75 \cdot 10^{-12} + 1 \cdot 10^{-6} x \text{ (Farads)}. \quad (2)$$

### 2.2 Conditioning circuit operation

The role of the conditioning circuit is to manage the electrical charge flow on the variable capacitor. The circuit proposed in [7] is composed of the charge pump and the flyback circuit (Fig. 2).

The role of the charge pump is to transfer the charges from  $C_{res}$  to  $C_{store}$ , and since  $C_{res} \gg C_{store}$ , the system will have more electrical energy than before, after the pumping. The role of the flyback circuit is twofold: put the charge pump back to the initial state, and transfer the harvested energy on the reservoir capacitor ( $C_{res}$ ). The operation of this conditioning circuit was described in detail in [3][7].

Switching between the flyback and the pump charge is driven by the event corresponding to the crossing of threshold values by the voltage  $V_{store}$ , and can be modeled by a finite-state automaton with one bit memory register [3].

## 3. SYSTEMC-AMS MODELING OF THE HARVESTER

### 3.1 Resonator modeling

The Newtonian differential equation of the resonator was modeled as a feedback TDF system (Fig. 3).

To define the operation of the resonator, two input values have to be provided: the voltage of the transducer's capacitor ( $V_{var}$ ), and the external acceleration ( $a_{ext}$ ). The output value of this block is the capacitance of the transducer,

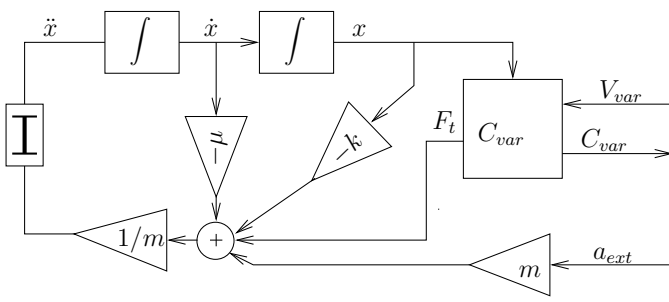


Figure 3: TDF diagram of the resonator.

which is related to the displacement by an algebraic function (block  $C_{var}$ ).

This block is implemented as a SystemC module (specified as `SC_MODULE` in the code). The delay at the input of the first integrator is required by the SystemC TDF solver which doesn't tolerate delayless loops.

### 3.2 Implementation of the conditioning circuit model

The conditioning circuit contains several components whose modeling is tricky. In the following sections we describe it for each block.

#### 3.2.1 Variable capacitor

The SystemC-AMS linear electrical circuit modeling tool provides a model of a variable linear capacitor. This is the most important component for our application, thus we conducted several simple test cases before incorporating it in a complex model. The main question was whether or not the variable capacitor model was charge conservative. For example, if the capacitor voltage is fixed, variations of the capacitance must provoke an electrical current in the voltage source.

The response to this question was positive. Indeed, in SystemC-AMS, when a variable capacitor is added to the circuit, two state variables are created: the capacitor voltage and the charge equal to the product of the capacitance and the voltage.

A variable capacitor is controlled by a signal issued from the TDF domain. Thus, it is natural to connect the signal  $C_{var}$  issued from the Fig. 3 model to the input of the variable capacitor.

#### 3.2.2 Diode implementation

The implementation of the diodes is the most challenging part of the modeling task, since they have a very non-linear behaviour. At first, we tried to model the diodes as current sources controlled by their own voltage with a given functional relation between both values. The implemented scheme is given in Fig. 4a. The voltage on the diode is measured in the linear electrical domain and converted to the TDF domain using the predefined SystemC-AMS block `sca_vd2sdf` (Voltage Difference To Signal Data Flow). Then the current is calculated and after a necessary loop delay, the source current is updated.

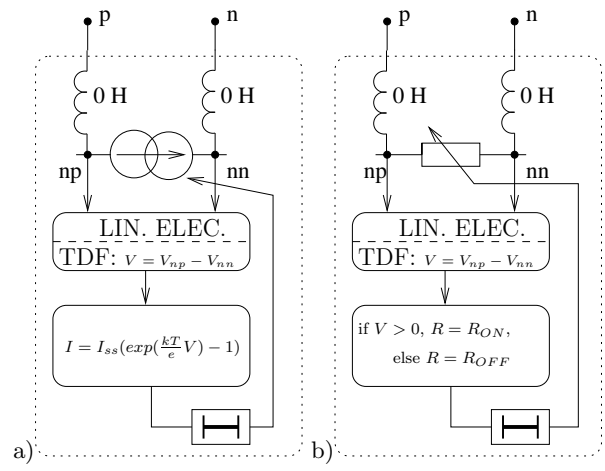


Figure 4: Different implementations of a diode in SystemC-AMS.

The 0 Henry inductors are necessary if one wants to encapsulate the diode implementation and allow the higher-level blocks to manage a diode as a two-terminal electrical component. In the SystemC-AMS structure, it is not possible to connect an internal electrical node to an external terminal. Since  $np$  and  $nn$  are internal nodes (they implement two electrical connections), a fictive inductor (which behaves as a wire) must be added to allow a connection from one of its terminals to the external terminal. We used inductors instead of zero resistances, since while the conductance matrix is generated, there is a division on the resistor values and a zero resistor yields a division by zero.

Although correct in theory, the presented diode model did not work, mainly because of the very steep exponential I-V diode characteristic in conjunction with the fixed delay between the voltage measurement and the current generation. So, if at step  $k$  the voltage becomes, say, 1 V, the corresponding very high current will be generated throughout the whole time step  $k + 1$ , which will definitively cause the modeling process to fail.

For this reason, we proposed a different scheme using a variable resistance (Fig. 4b). In this case, the diode is modeled as a switch with "on" and "off" resistances, and switching is ordered by the voltage on the switch itself. Although the value of the resistance will also be updated with a one time step delay after the voltage change, there is no delay between the current and the voltage calculation, thus the model is accurate enough if the time step is low.

The listing of the diode implementation is given below.

It is also possible to implement a more complex model, taking into account the non-zero diode threshold, adding a voltage source in series with the resistor. In this case, the ON/OFF TDF signal should simultaneously change the resistance value and the source voltage.

```
//TDF block that calculates the state of the diode
SCA_SDF_MODULE(Electrical_diode_function) {
  sca_sdf_in <double> voltage;
```

```

sca_sdf_out<double> resistance;
void sig_proc()
{
//calculates the resistance using the voltage
}
void attributes()
{
//one delay step for the exit signal
current.set_delay(1);
}
//constructor ...
};
SCMODULE(Electrical_diode) {
//external connections
sca_elec_port p, n;

Electrical_diode(sc_module_name name_)
: sc_module(name_) {
//definition of the 0H inductors
sca_l* in_ind = new sca_l("in_ind",0.);
sca_l* out_ind = new sca_l("out_ind",0.);

//definition of the variable resistor
sca_sdf2r* resistor = new sca_sdf2r("resistor");

//definition of the converter LIN ELEC to TDF
//converts the voltage across the resistor
// (diode) to a TDF signal (double)
sca_vd2sdf* converter =
new sca_vd2sdf("converter");

//definition of the resistance function
Electrical_diode_function* function =
new Electrical_diode_function("function");

//definition of internal electrical nodes
sca_elec_node np, nn;

//definition of internal signals
sca_sdf_signal<double> voltage, current;

//connect inductors
in_ind->n(p);
in_ind->p(np);
out_ind->n(nn);
out_ind->p(n);

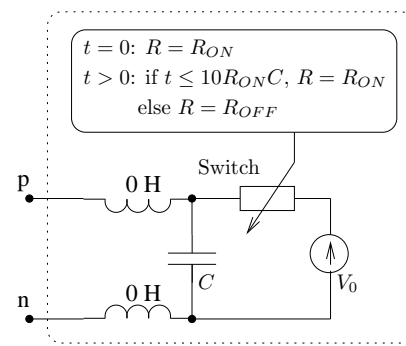
//connect converter
converter->p(np);
converter->n(nn);
converter->sdf_voltage(voltage);

//connect diode function
function->voltage(voltage);
function->current(current);

//connect the variable resistor
resistor->p(np);
resistor->n(nn);
resistor->ctrl(current);
}
};

```

This model is used as a normal SystemC-AMS component. For example, an insertion of a diode between the nodes  $p$



**Figure 5: Implementation of a capacitor with initial pre-charge.**

and  $n$  is achieved as follows:

```

Electrical_diode diode("diode");
sca_elec_node p, n;
diode.p(p);
diode.n(n);

```

### 3.2.3 Initial charge of the capacitors

In the modeling of power electronic systems, it is very important to be able to control the initial energy of the reactive elements. In SystemC-AMS, default values are zero, and no mechanism is proposed to modify them.

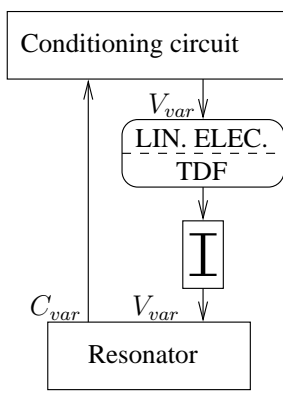
Thus for each capacitor, we use the scheme shown in Fig. 5. A voltage source was connected during several step periods to the capacitor through a switch (variable resistance). The calculation of the initial pre-charge time is encapsulated in the model. The switch is on during at least the first time step, then, the time constant is calculated (the  $RC$  product), and if the latter is high, the switch stays on during the time equal to at least  $10RC$ .

### 3.2.4 Conditioning circuit/flyback switch modeling

As shown in [3], the switch should be driven by the energy state of the pump charge. Thus in our model we implemented a switch as a finite-state automaton (with 2 possible states), driven by the events of threshold-crossing by the voltage  $V_{store}$ . The switch becomes "on" when it is "off" and when the  $V_{store}$  voltage crosses some  $V_1$  threshold, and the switch becomes "off" when it is "on" and the  $V_{store}$  voltage crosses some  $V_2$  threshold,  $V_1 < V_2$ .

### 3.2.5 Modeling of the diode D3 switching

A particular problem arises in the modeling of the circuit behaviour when the the flyback/charge pump switch is turning off. Before this moment, the current in the inductor is maximal. When the switch turns off, the current path is broken, which normally, provokes a high negative voltage on the inductor. Since the voltage of the left node of the inductor is fixed by the  $C_{res}$  capacitor, a negative voltage glitch is generated on D3. However, the latter is connected so as to turn on when a negative voltage is generated on the node *fly*. By turning on, the D3 diode allows the inductor current to continue. One can say that the D3 diode "absorbs" the negative voltage glitch.



**Figure 6: Diagram of the complete harvester model in the SystemC-AMS language.**

**Table 1: Numerical values of modeling test case**

$k$ , $\text{nm}^{-1}$	$m$ $\text{kg}$	$\mu$ , $\text{Nsm}^{-1}$	$\omega$ , $\text{rad}\cdot\text{s}^{-1}$	$a_{ext}$ , $\text{ms}^{-2}$
152.6	46e-6	2.19e-3	$2\pi\cdot 298$	$10\cdot\sin(\omega t)$
$C_{res}$ , F	$C_{store}$ , F	$C_p$ , F	$L$ , H	$R_L$ , $\Omega$
$10^{-6}$	$3.3\cdot 10^{-9}$	$10^{-13}$	$2.5\cdot 10^{-3}$	$10^{-1}$
$\Delta t$ , s	$R_{ONDI}$ , $\Omega$	$R_{OFFDI}$ , $\Omega$	$R_{ONSW}$ , $\Omega$	$R_{OFFSW}$ , $\Omega$
$4\cdot 10^{-9}$	$10^{-9}$	$10^{10}$	1	$10^{11}$
Switch low threshold, $V_1$ , V		Switch high threshold $V_2$ , V		
6		11		

However, the described phenomenon takes place instantaneously, whereas the model in SystemC-AMS is strictly causal: for the diode D3 to turn on, its voltage should become negative during the preceding step. Since the switching off is abrupt (the off resistance of the switch is high), the generated voltage is very high and being present throughout the step, seriously disturbs the circuit's state vector.

To limit this negative effect, we connected the node *fly* to a small parallel-to-ground capacitor  $C_p = 1\text{pF}$ , whose role is to maintain the voltage on the node *fly* at a reasonable level during the transition step. Adding this capacitor doesn't invalidate the model, since it naturally models the node parasitical capacitance.

When the switch turns off, the current continues to flow through the capacitor  $C_p$ , charging it at a negative voltage, and at the next step the diode turns on and the circuit operates normally.

### 3.3 Model of the complete system

The model of the global system is presented in Fig. 6: it is composed of the conditioning circuit and the resonator models, connected through the input and output values. The delay is necessary since there is a loop, a *sca\_v2sdf* block converts the voltage of  $C_{store}$  capacitor to the TDF domain.

## 4. MODELING RESULTS

### 4.1 Description of the modeling experiment

Table 1 gives the numerical values for the circuit modeling. With a time step of 4 ns, a 1 s simulation requires 250 million steps. Such a small step was chosen to accurately model the quick processes taking place, involving highly non-linear elements (diodes).

In the first version of our model, the capacitance of the variable capacitor  $C_{var}$ , calculated by the TDF resonator, was updated in the LIN ELEC domain at each step (every 4 ns). This required a reinitialization of the network matrix at each step, leading to an excessively long simulation time (the linear solver of SystemC-AMS is optimized for modeling time-invariant systems, or systems whose parameters change rarely).

This problem was identified using the GNU profiler (*gprof*). Therefore, we modified the variable capacitor's mixed TDF-LIN ELEC model: in the new version, the LIN ELEC capacitance value is updated only one time every 400 ns. This modification does not affect the accuracy of the model, since the capacitance varies sinusoidally with a frequency of only 298 Hz. This optimisation made the simulation run about 9 times faster.

With this modification, modeling 1 second of system operation required 140 minutes of machine time on Mac OS X 10.4, Intel Core 2 Duo, 2.0 GB, 4 MB Cache, 2 GHz clock computer (only one processor core was used to run the simulation). SystemC 2.2.0 and SystemC-AMS 0.15 RC5 were used.

Fig. 7 presents the global view of the simulation results, showing the evolution of  $V_{store}$  and  $V_{res}$  during 1 s. This is typical behaviour for a charge pump, apparently identical to the results obtained by the VHDL-AMS simulation [3] (for this reason we provide the plot of the evolution of only two important value,  $V_{store}$  and  $V_{res}$ , for the other the plots are identical with those given in [3]). Namely, the evolution of  $V_{res}$  highlights an accumulation of the harvested energy in the system.

### 4.2 Modeling results validation

To verify our model we compared the SystemC-AMS model with a VHDL-AMS and a Matlab Simulink model. The former was described in [3], the latter was created using the electrical network equations.

The values of three system quantities were compared:  $V_{store}$ ,  $V_{res}$  and  $I_L$  (the quantity defining the energy state of the system). From the results of each model,  $V_{store}$  was measured every 10 ms to compare global system operation,  $V_{res}$ 's peak value minus 5V (the initial charge) was measured after three cycles of the charge pump/flyback operation to compare only the energy gain, and for  $I_L$  the peak value was taken from the first cycle to compare the flyback operation. We also performed a number of other global and detailed tests, in which SystemC-AMS showed similar results as Simulink (under 2% relative difference).

Every model used the same block parameters (resistances, initial voltages,...), but with different diode models. Simulink used a quadratic diode law, whereas VHDL-AMS used a model with 3 zones (linear on and off zones, and a quadratic

**Table 2: Relative differences in comparison with VHDL-AMS**

	$V_{store}$	$V_{res}$	$I_L$
SystemC-AMS	0.495%	1.468%	0.595%
Simulink	0.886%	0.316%	0.100%

transition zone to keep the first derivative continuous). The VHDL-AMS model did not include the  $C_p$  capacitor, as it caused the simulation to slow down too much.

Table 2 presents the relative differences of Simulink and SystemC-AMS modeling versus VHDL-AMS modeling.

These results show that the SystemC-AMS model is correct. The use of various diode models is reflected in the different energy yields (reflected by the values of  $V_{res}$  after 4 cycles). Nonetheless, these differences are very small (less than 2%), with Simulink's energy gain being a bit closer to VHDL-AMS's, due to Simulink's diode model being more similar to that of VHDL-AMS.

Simulation times were 3.5 minutes for Matlab Simulink using the *ode23s* solver on a Dual Intel Xeon 3Ghz (4 cores) with 6Gb of memory and 5.75 minutes for VHDL-AMS using the ADVance MS simulator on a Sun Ultra-80.

Compared with SystemC-AMS modeling, Simulink and VHDL-AMS simulations consume much less machine time. This is explained by the fact, that the corresponding solvers use a variable simulation step, allowing a dramatical time step reduction only during the flyback circuit operation. The SystemC-AMS model uses a fixed step, which is adjusted to accurately model the quickest process of the system.

## 5. CONCLUSION

This study presented a complex SystemC-AMS model of a vibration energy harvester with a capacitive transducer. It was demonstrated that complex non-linear electrical circuits coupled with non-electrical domain subsystems can be accurately modeled with SystemC-AMS. The modeling results were compared with VHDL-AMS and Simulink simulation output.

The main limitation of the current version of the SystemC-AMS simulator for modeling complex AMS systems is the impossibility to vary dynamically the simulation step. Also, if a time-variable linear system is modeled with the LIN ELEC solver, the equation system matrix is reinitialized at each variation of the system parameters. This initialization is a very time-consuming operation which, if executed at each time step, can dramatically increase the simulation time.

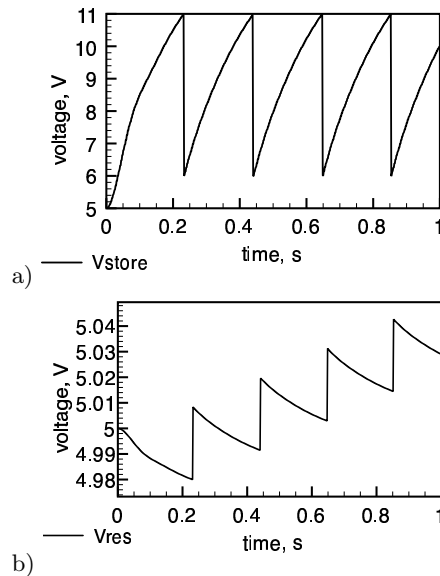
Nevertheless, SystemC-AMS, being a SystemC extension, offers the unique possibility to model systems from the hardware level (electrical circuit) up to the software level using the same standardised language (C++). As SystemC and SystemC-AMS are both based on C++ and open source, all C/C++ features, tools and libraries are available to the user (eg. the GNU profiler).

## 6. ACKNOWLEDGMENTS

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**Figure 7: Global view of the harvesting operation. a)  $V_{store}$  voltage, b)  $V_{res}$  voltage evolution, highlighting the energy accumulation.**